

# IPB80P04P4L04ATMA1

#### IPB80P04P4L04ATMA1 Information



For Reference Only

Part Number IPB80P04P4L04ATMA1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH TO263-3

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## IPB80P04P4L04ATMA1 Specifications

Manufacturer Part Number         IPB80P04P4L04ATMA1           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Fackage         To-263-3, D2Pak (2 Leads + Tab), TO-263AB           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.2V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         176n C@ 10V           Input Capacitance (Ciss) (Max) @ Vds         3800p F@ 25V           Vgs (Max)         ±16V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         4.4 mOhm @ 80A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         PG-TO263-3-2           Package / Case         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesAutomotive, AEC-Q101, OptiMOS?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs176nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3800pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs4.4 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	IPB80P04P4L04ATMA1
Fackage         Transistors - FETs, MOSFETs - Single           Package         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.2V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         176nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3800pF @ 25V           Vgs (Max)         ±16V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         4.4 mOhm @ 80A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         PG-TO263-3-2           Package / Case         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer	Infineon Technologies
Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series Automotive, AEC-Q101, OptiMOS? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 176nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3800pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 4.4 mOhm @ 80A, 10V Operating Temperature Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Category	Discrete Semiconductor Products
SeriesAutomotive, AEC-Q101, OptiMOS?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs176nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3800pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs4.4 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs176nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3800pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs4.4 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-T0263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  BOA (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Surplier Device Package  PG-TO263-3-2  Package / Case  MOA (Tc)  80A (Tc)  80B	Series	Automotive, AEC-Q101, OptiMOS?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  B0A (Tc)  Prive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  PG-TO263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C       80A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.2V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       176nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3800pF @ 25V         Vgs (Max)       ±16V         FET Feature       -         Power Dissipation (Max)       125W (Tc)         Rds On (Max) @ Id, Vgs       4.4 mOhm @ 80A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       PG-TO263-3-2         Package / Case       TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs176nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3800pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs4.4 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id       2.2V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       176nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3800pF @ 25V         Vgs (Max)       ±16V         FET Feature       -         Power Dissipation (Max)       125W (Tc)         Rds On (Max) @ Id, Vgs       4.4 mOhm @ 80A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       PG-TO263-3-2         Package / Case       TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs       176nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3800pF @ 25V         Vgs (Max)       ±16V         FET Feature       -         Power Dissipation (Max)       125W (Tc)         Rds On (Max) @ Id, Vgs       4.4 mOhm @ 80A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       PG-TO263-3-2         Package / Case       TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±16V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.4 mOhm @ 80A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  PG-TO263-3-2  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	2.2V @ 250μA
Vgs (Max) ±16V  FET Feature -  Power Dissipation (Max) 125W (Tc)  Rds On (Max) @ Id, Vgs 4.4 mOhm @ 80A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Surface Mount  Supplier Device Package PG-TO263-3-2  Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	176nC @ 10V
FET Feature -  Power Dissipation (Max) 125W (Tc)  Rds On (Max) @ Id, Vgs 4.4 mOhm @ 80A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Surface Mount  Supplier Device Package PG-TO263-3-2  Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	3800pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.4 mOhm @ 80A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  PG-TO263-3-2  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs4.4 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  PG-TO263-3-2  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	125W (Tc)
Mounting Type Surface Mount  Supplier Device Package PG-TO263-3-2  Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	4.4 mOhm @ 80A, 10V
Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	PG-TO263-3-2
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

### IPB80P04P4L04ATMA1 Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPB80P04P4L04ATMA1 Payment Methods



















## IPB80P04P4L04ATMA1 Shipping Methods













If you have any question about IPB80P04P4L04ATMA1, please do not hesitate to contact us!

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